

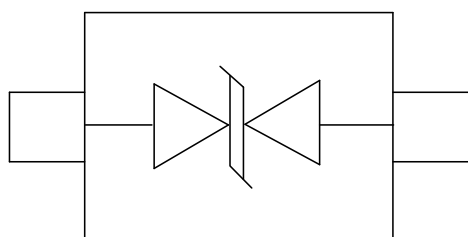
Description

The DCSDXXC-H is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers and PDA's, using monolithic silicon technology to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DCSDXXC-H complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. The DCSDXXC-H is assembled into a lead-free SOD-323 package and will protect one unidirectional line. These devices will fit on the same PCB pad area as an 0805 MLV device.

Mechanical Characteristics

- ◆ Package: SOD-323
- ◆ Lead Finish: Matte Tin
- ◆ Case Material: "Green" Molding Compound.
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Marking	Packaging	Reel Size
DCSDXXC-H	XX	3000/Tape & Reel	7 inch

Features

- ◆ 500W peak pulse power (8/20 μs)
- ◆ Protects one data or power line
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage:
3.3V, 5V, 8V, 12V, 15V, 24V, 36V, 40V
- ◆ Ultra low clamping voltage
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
- ◆ RoHS Compliant

Applications

- ◆ Cellular Handsets and Accessories
- ◆ Personal Digital Assistants
- ◆ Notebooks and Handhelds
- ◆ Portable Instrumentation
- ◆ Peripherals
- ◆ Pagers Peripherals
- ◆ Desktop and Servers

Marking Information



XX = Device Marking Code

Part Number	Marking
DCSD33C-H	33
DCSD05C-H	05
DCSD08C-H	08
DCSD12C-H	12
DCSD15C-H	15
DCSD18C-H	18
DCSD24C-H	24
DCSD36C-H	36
DCSD40C-H	40

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	500	W
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

DCSD33C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Breakdown Voltage	VBR	3.8			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	VRWM = 3.3V
Clamping Voltage	VC			5	V	IPP = 1A (8 x 20 μs pulse)
Clamping Voltage	VC			12.5	V	IPP = 40A (8 x 20 μs pulse)
Peak Pulse Current	Ipp			40	A	tp = 8/20 μs
Junction Capacitance	CJ		120	200	pF	VR = 0V, f = 1MHz

DCSD05C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	VRWM = 5V
Clamping Voltage	VC			9.5	V	IPP = 1A (8 x 20 μs pulse)
Clamping Voltage	VC			15	V	IPP = 34A (8 x 20 μs pulse)
Peak Pulse Current	Ipp			34	A	tp = 8/20 μs
Junction Capacitance	CJ		110	200	pF	VR = 0V, f = 1MHz

DCSD08C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			8	V	
Breakdown Voltage	VBR	8.5			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 8V
Clamping Voltage	VC			10	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			16	V	I _{PP} = 32A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			32	A	tp = 8/20μs
Junction Capacitance	CJ		100	200	pF	VR = 0V, f = 1MHz

DCSD12C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			12	V	
Breakdown Voltage	VBR	13.3			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 12V
Clamping Voltage	VC			19	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			25	V	I _{PP} = 20A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			20	A	tp = 8/20μs
Junction Capacitance	CJ		60	100	pF	VR = 0V, f = 1MHz

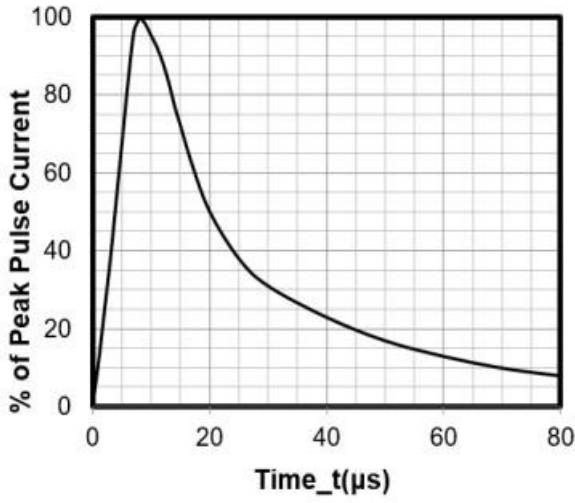
DCSD15C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.7			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 15V
Clamping Voltage	VC			20	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			25	V	I _{PP} = 16A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			16	A	tp = 8/20μs
Junction Capacitance	CJ		30	80	pF	VR = 0V, f = 1MHz

DCSD18C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			18	V	
Breakdown Voltage	VBR	19.8			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 18V
Clamping Voltage	VC			25	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			38	V	I _{PP} = 13A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			13	A	t _p = 8/20μs
Junction Capacitance	C _J		30	60	pF	VR = 0V, f = 1MHz

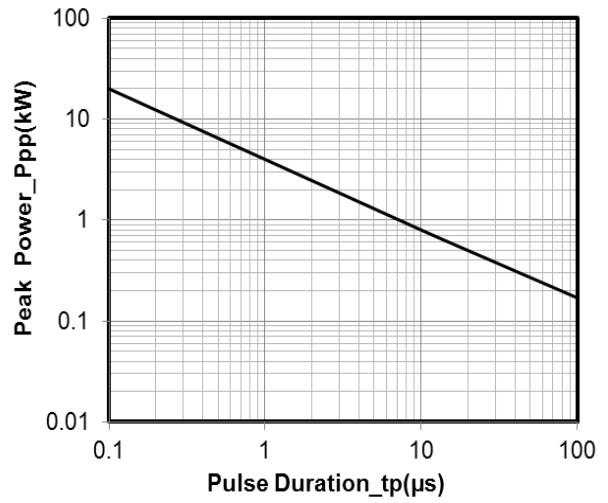
DCSD24C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 24V
Clamping Voltage	VC			40	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			50	V	I _{PP} = 10A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			10	A	t _p = 8/20μs
Junction Capacitance	C _J		30	50	pF	VR = 0V, f = 1MHz

DCSD36C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			36	V	
Breakdown Voltage	VBR	38			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 36V
Clamping Voltage	VC			48	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			83	V	I _{PP} = 6A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			6	A	tp = 8/20μs
Junction Capacitance	CJ		20	30	pF	VR = 0V, f = 1MHz

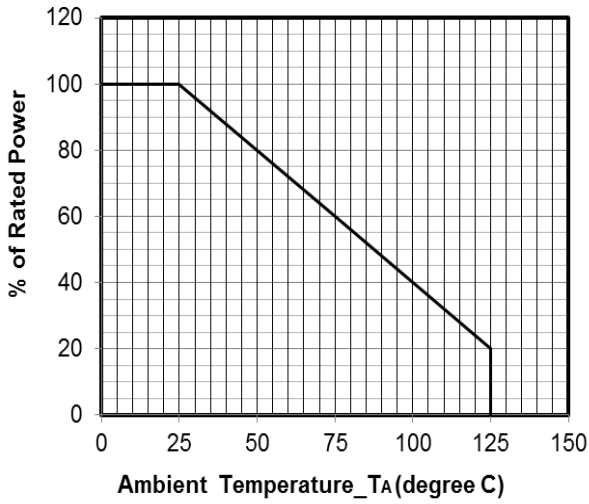
DCSD40C-H						
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			40	V	
Breakdown Voltage	VBR	44			V	IT = 1mA
Reverse Leakage Current	IR			0.2	μA	VRWM = 40V
Clamping Voltage	VC			50	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	VC			100	V	I _{PP} = 5A (8 x 20μs pulse)
Peak Pulse Current	I _{pp}			5	A	tp = 8/20μs
Junction Capacitance	CJ		20		pF	VR = 0V, f = 1MHz



8 X 20μs Pulse Waveform

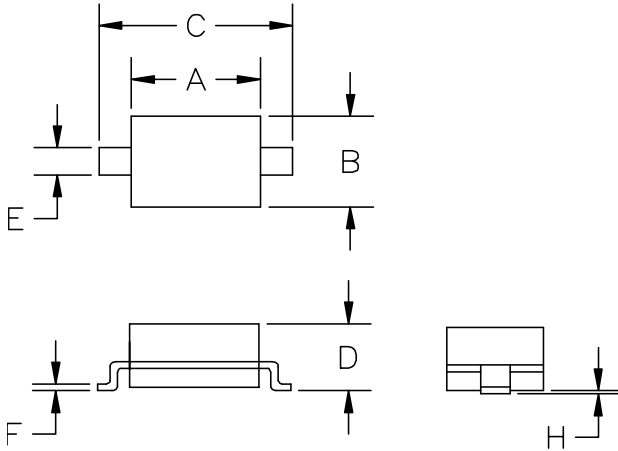


Peak Pulse Power vs. Pulse Time



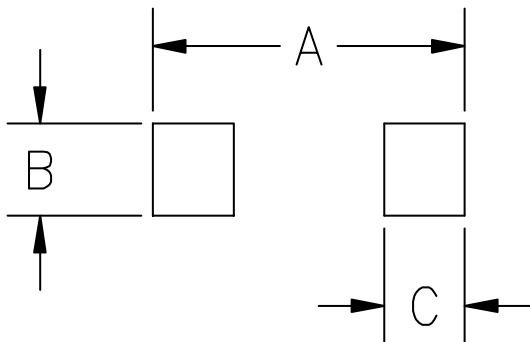
Power Derating Curve

SOD-323 Package Outline Drawing



SYM	DIMENSIO			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.80	0.060	0.071
B	1.20	1.40	0.045	0.054
C	2.30	2.70	0.090	0.107
D	-	1.10	-	0.043
E	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
H	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

Contact Information

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